## NSN 5961-00-023-6219

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View Online at https://aerobasegroup.com/nsn/5961-00-023-6219 **Inclosure Material:** Metal **Overall Length:** Between 0.330 inches and 0.505 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.544 inches and 0.562 inches **Thread Size:** 0.250 inches **Criticality Code Justification:** Feat **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 200.0 breakover voltage, dc **Current Rating Per Characteristic:** 150.00 amperes forward current, average absolute **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Item must comply with requirements of desc production standard no. L00916; for navy nuclear propulsion plant products only; junction pattern arrangement: pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure:** 

No

Demilitarization:

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